

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF329** is Designed for Wide Band Large-Signal Output and Driver Amplifier Stages in the 100-500 MHz Frequency Range.

FEATURES INCLUDE:

- Gold Metalization
- **3:1 VSWR**
- **I/O** Network Matching

MAXIMUM RATINGS

I_C	9.0 A (CONT) 12.0 A (PEAK)
V_{CB}	60 V
P_{DISS}	270 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+150^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.65°C/W

PACKAGE STYLE .400X.425" 6L FLG.	
	1 & 3 = EMITTER 2 = COLLECTOR 4 = BASE

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 80\text{ mA}$	60			V
BV_{CES}	$I_C = 80\text{ mA}$	60			V
BV_{CEO}	$I_C = 80\text{ mA}$	30			V
BV_{EBO}	$I_E = 8.0\text{ mA}$	4.0			V
I_{CBO}	$V_{CB} = 30\text{ V}$			5.0	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 4.0\text{ A}$	20		80	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$		95	125	pF
G_{PE} η	$V_{CC} = 28\text{ V}$ $P_{out} = 100\text{ W}$ $f = 400\text{ MHz}$	7.0 50	9.7 60		dB %
ψ	$V_{CC} = 28\text{ V}$ $P_{out} = 100\text{ W}$ $f = 400\text{ MHz}$ $V_{SWR} = 3:1$ ALL PHASE ANGLES	NO DEGRADATION IN OUTPUT POWER			

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Specifications are subject to change without notice.

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